isc Silicon NPN RF Transistor 2SC2757

DESCRIPTION

- Low Noise
- High Current-Gain Bandwidth Product

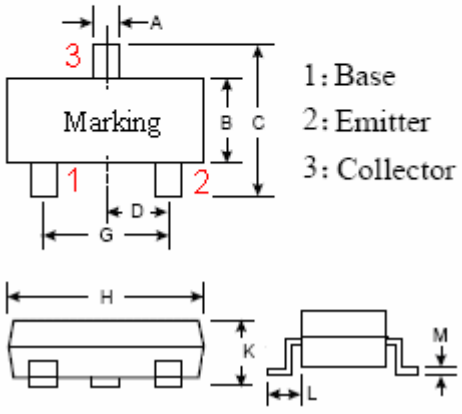
APPLICATIONS

- Designed for use in VHF RF amplifier, local oscillator, mixer.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	50	mA
P_C	Collector Power Dissipation @T_C=25℃	0.15	W
T_J	Junction Temperature	125	℃
T_{stg}	Storage Temperature Range	-55~125	℃

SOT-23-3L package



DIM	mm	
	MIN	MAX
A	0.30	0.40
B	1.50	1.70
C	2.65	2.95
D	0.95	
G	1.80	2.00
H	2.82	3.02
K	1.05	1.25
L	0.70	
M	0.10	0.20

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 10mA ; I_B= 1mA			0.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 12V; I_E= 0			0.1	μA
h_{FE}	DC Current Gain	I_C= 5mA ; V_{CE}= 10V	60		240	
f_T	Current-Gain—Bandwidth Product	I_C= 5mA ; V_{CE}= 10V	800	1100		MHz
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 10V;f= 1.0MHz			1.5	pF
$r_{bb'}$ • CC	Base Time Constant	I_C= 5mA ; V_{CB}= 10V;f= 31.9MHz		10	15	ps

◆ **h_{FE} Classifications**

Marking	T32	T33	T34
h_{FE}	60-120	90-180	120-240